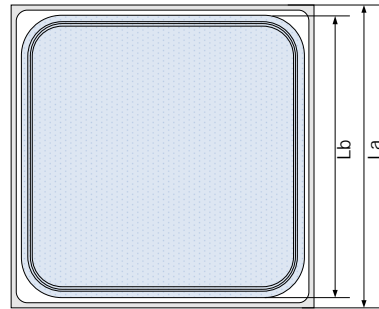


2SB035030MLJY SCHOTTKY BARRIER DIODE CHIPS
DESCRIPTION

- Ø 2SB035030MLJY is a schottky barrier diode chips fabricated in silicon epitaxial planar technology;
- Ø Low power losses, high efficiency;
- Ø Guard ring construction for transient protection;
- Ø High ESD capability;
- Ø High surge capability;
- Ø Packaged products are widely used in switching power suppliers, polarity protection circuits and other electronic circuits;
- Ø Chip Size:350 μ m X 350 μ m;
- Ø Chip Thickness: 155 \pm 20 μ m


Chip Topography and Dimensions

 La: Chip Size: 350 μ m;

 Lb: Pad Size: 300 μ m;

ORDERING SPECIFICATIONS

Product Name	Specification
2SB035030MLJY	For Au and AlSi wire bonding package

ABSOLUTE MAXIMUM RATINGS

Parameters	Symbol	Ratings	Unit
Maximum Repetitive Peak Reverse Voltage	VRRM	30	V
Average Forward Rectified Current	IFAV	200	mA
Peak Forward Surge Current@8.3ms	IFSM	1	A
Maximum Operation Junction Temperature	TJ	125	$^{\circ}$ C
Storage Temperature Range	TSTG	-40~125	$^{\circ}$ C

ELECTRICAL CHARACTERISTICS (Tamb=25 $^{\circ}$ C)

Parameters	Symbol	Test Conditions	Min.	Max.	Unit
Reverse Voltage	VBR	IR=0.1mA	30	--	V
Forward Voltage	VF	IF=200mA	--	0.50	V
Reverse Current	IR	VR=10V	--	30	μ A